

IN THE SPECIFICATION:

Please replace the paragraph beginning on Page 1, line 6 with the following paragraph:

The United States Government has certain rights in this invention. This invention was made under a CRADA (CRADA No. BG-00-441) between American
B1 Superconductor Corporation and Lawrence Berkeley National Laboratory operated for the United States Department of Energy.

Please replace the paragraph at page 16, line 1 with the following paragraph:

b7 A crystallizable layer used in the methods of the invention can comprise any material that is capable of attaining crystalline structure, and thereby form a crystalline active layer. Such crystallizable layers include metals, mixed metals, rare earths, alkaline earths, semiconductors and compounds of same, including oxides, carbides, nitrides, borides, sulfides, chalcogenides and halides, and the like. A crystallizable layer can also include organic materials, such as organic polymers. Exemplary materials which the crystallizable layer can comprise include high temperature superconductors such as $\text{YBa}_2\text{Cu}_3\text{O}_{7-\delta}$ (where δ is greater than 0 and less than 0.5), $\text{REZ}_2\text{Cu}_3\text{O}_{7-\delta}$ (where RE is a rare earth or yttrium, Z is an alkaline earth element, and δ is greater than 0 and less than 0.5), Bi-Sr-Ca-Cu-O, Ti-Ba-Ca-Cu-O, and the like; oxides such as SrTiO_3 , Y_2O_3 , RuO_2 , ZrO_2 , SiO_2 , yttria-stabilized zirconia (YSZ), CeO_2 , Al_2O_3 , and the like; semiconductors such as Si, Ge, InP, GaSb, InSb, GaAs, InAs, (In,Ga)As, CdS, and the like; magnetic and magnetorestrictive materials such as LaMnO_3 , Fe, NiO, Co, Ni, and the like; coatings for tribological or hardness applications such as SiC, TiN, diamond and diamond-like coatings, and the like, and sensor materials such as ZnO, lead-zirconite-titanate, and the

Dzard like.

Please replace the paragraph at page 17, line 15 with the following paragraph:

bb A crystallizable underlayer used in the methods of the invention can comprise any material that is capable of attaining crystalline structure, and can be either a layer deposited above the substrate but below the nucleating surface or can be the substrate itself. Such crystallizable underlayers include metals, mixed metals, rare earths, alkaline earths, semiconductors and compounds of same, including oxides, carbides, nitrides, borides, sulfides, chalcogenides and halides, and the like. A crystallizable underlayer can also include organic materials, such as organic polymers. Exemplary materials which the crystallizable underlayer can comprise include high temperature superconductors such as $\text{YBa}_2\text{Cu}_3\text{O}_{7-\delta}$ (where δ is greater than 0 and less than 0.5), $\text{REZ}_2\text{Cu}_3\text{O}_{7-\delta}$ (where RE is a rare earth or yttrium, Z is an alkaline earth element, and δ is greater than 0 and less than 0.5), Bi-Sr-Ca-Cu-O, Ti-Ba-Ca-Cu-O, and the like; oxides such as SrTiO_3 , Y_2O_3 , RuO_2 , ZrO_2 , SiO_2 , yttria-stabilized zirconia (YSZ), CeO_2 , Al_2O_3 , and the like; semiconductors such as Si, Ge, InP, GaSb, InSb, GaAs, InAs, (In,Ga)As, CdS, and the like; magnetic and magnetorestrictive materials such as LaMnO_3 , Fe, NiO, Co, Ni, and the like; coatings for tribological or hardness applications such as SiC, TiN, diamond and diamond-like coatings, and the like, and sensor materials such as ZnO, lead-zirconite-titanate, and the like.

